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NTD5804N, NTDV5804N, SVD5804N



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Power MOSFET

40 V, 69 A, Single N-Channel, DPAK

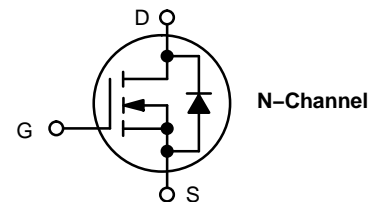
Features

- Low $R_{DS(on)}$
- High Current Capability
- Avalanche Energy Specified
- NTDV, STDV and SVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Applications

- CCFL Backlight
- DC Motor Control
- Class D Amplifier
- Power Supply Secondary Side Synchronous Rectification

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
40 V	12 m Ω @ 5.0 V	69 A
	7.5 m Ω @ 10 V	



MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

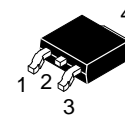
Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	40	V	
Gate-to-Source Voltage – Continuous		V_{GS}	± 20	V	
Gate-to-Source Voltage – Non-Repetitive ($t_p < 10 \mu\text{s}$)		V_{GS}	± 30	V	
Continuous Drain Current ($R_{\theta JC}$) (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	I_D	69	A
		$T_C = 100^\circ\text{C}$		49	
		$T_C = 25^\circ\text{C}$	P_D	71	W
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	125	A	
Operating Junction and Storage Temperature		T_J, T_{stg}	-55 to 175	$^\circ\text{C}$	
Source Current (Body Diode)		I_S	60	A	
Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 50 \text{ V}, V_{GS} = 10 \text{ V}, R_G = 25 \Omega, I_{L(pk)} = 36 \text{ A}, L = 0.3 \text{ mH}, V_{DS} = 40 \text{ V}$)		E_{AS}	195	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

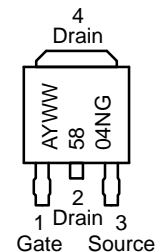
Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	2.1	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	106	

1. Surface-mounted on FR4 board using the minimum recommended pad size.



**DPAK
CASE 369C
(Surface Mount)
STYLE 2**

MARKING DIAGRAM & PIN ASSIGNMENT



A = Assembly Location*
Y = Year
WW = Work Week
5804N = Device Code
G = Pb-Free Package

* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NTD5804N, NTDV5804N, SVD5804N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	40	45		V	
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			41		mV/°C	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 40 V	T _J = 25°C			1.0	μA
			T _J = 150°C			100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V				±100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	2.0		3.5	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			7.3		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		5.7	7.5	mΩ
		V _{GS} = 5 V, I _D = 10 A		7.9	12	
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 15 A		12		S

CHARGES, CAPACITANCES AND GATE RESISTANCES

Input Capacitance	C _{iss}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 25 V		2460	2850	pF
Output Capacitance	C _{oss}			310	400	
Reverse Transfer Capacitance	C _{riss}			215	280	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 32 V, I _D = 30 A		45		nC
Threshold Gate Charge	Q _{G(TH)}			2.8		
Gate-to-Source Charge	Q _{GS}			10		
Gate-to-Drain Charge	Q _{GD}			12.6		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 10 V, V _{DD} = 32 V, I _D = 30 A, R _G = 2.5 Ω		11.8		ns
Rise Time	t _r			18.7		
Turn-Off Delay Time	t _{d(off)}			26.8		
Fall Time	t _f			5.9		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 10 A	T _J = 25°C		0.81	1.2	V
			T _J = 150°C		0.63		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 30 A		21.7		ns	
Charge Time	t _a			11.9			
Discharge Time	t _b			9.8			
Reverse Recovery Charge	Q _{RR}			11.8			nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

NTD5804N, NTDV5804N, SVD5804N

TYPICAL PERFORMANCE CHARACTERISTICS

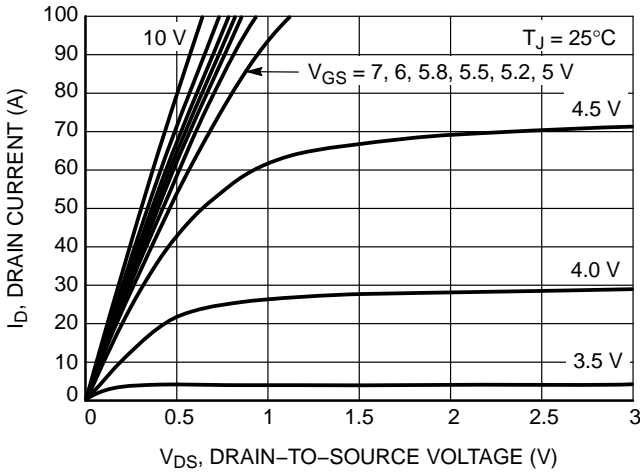


Figure 1. On-Region Characteristics

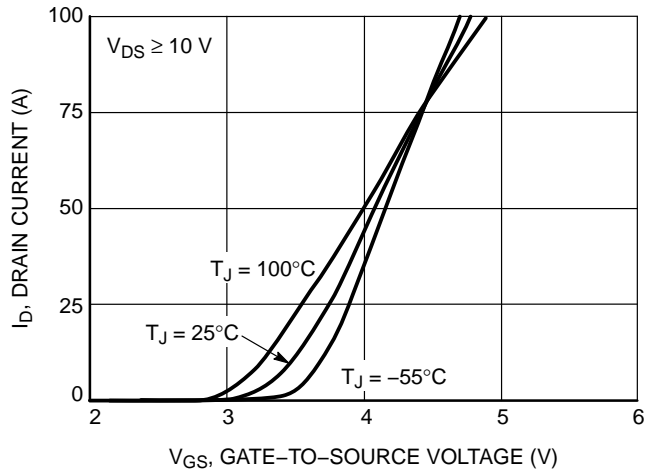


Figure 2. Transfer Characteristics

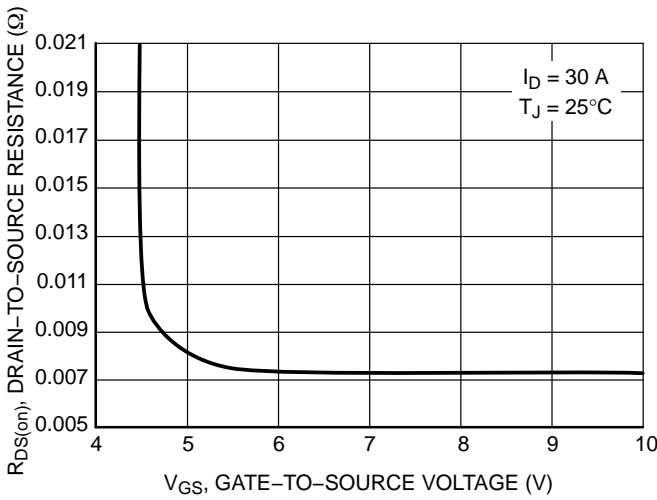


Figure 3. On-Resistance vs. Drain Current

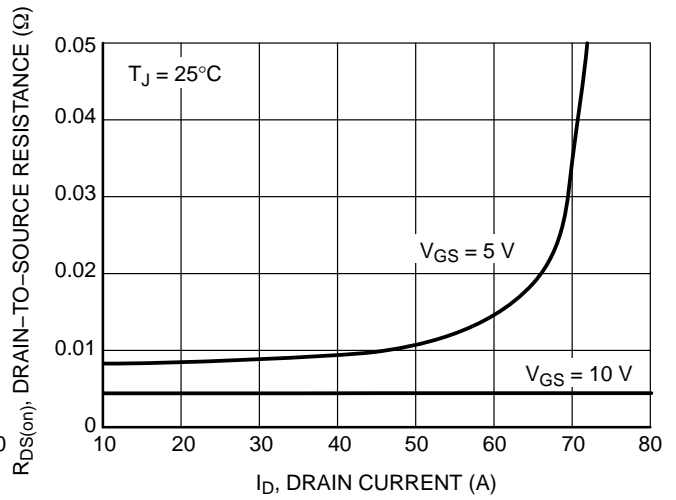


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

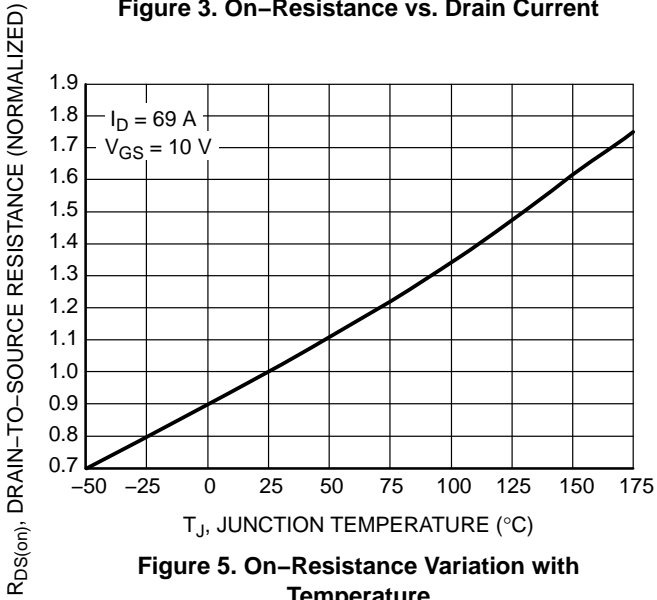


Figure 5. On-Resistance Variation with Temperature

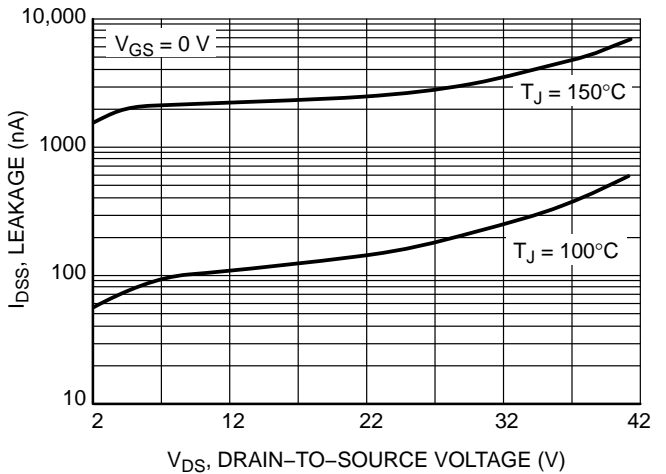


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CHARACTERISTICS

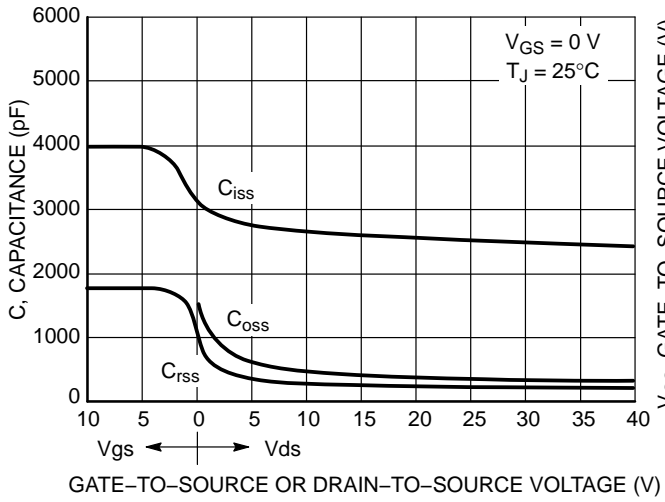


Figure 7. Capacitance Variation

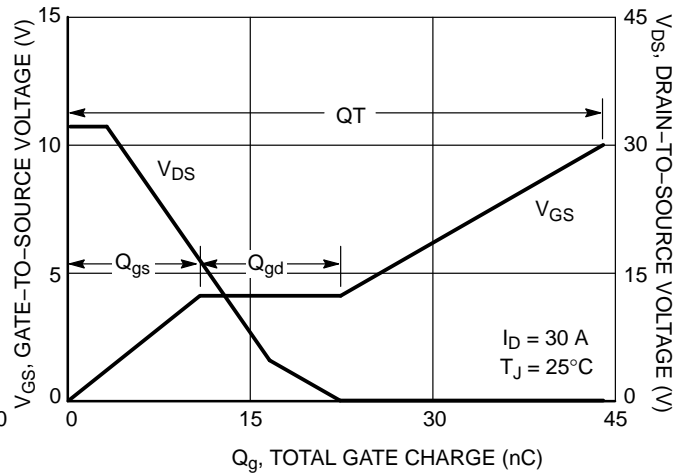


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

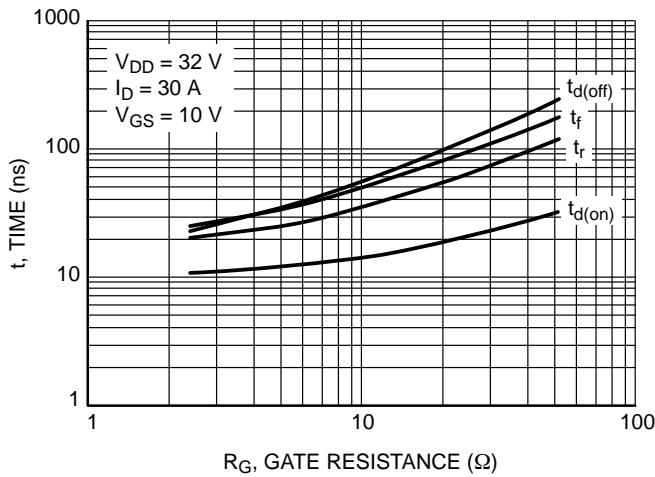


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

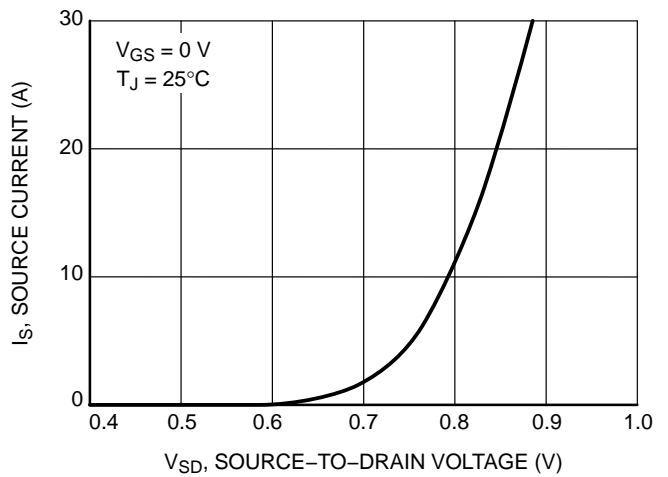


Figure 10. Diode Forward Voltage vs. Current

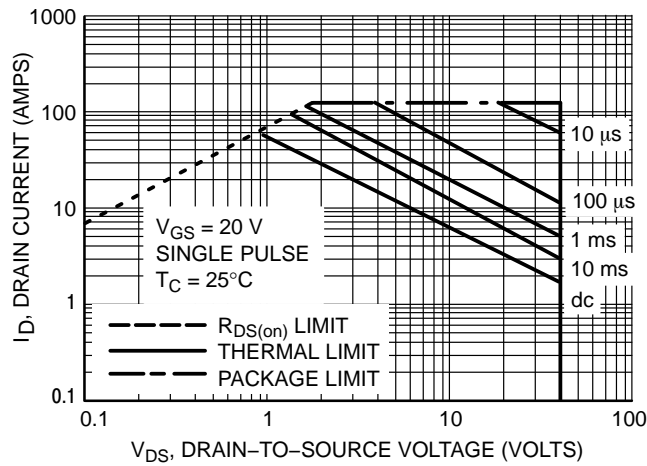


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NTD5804N, NTDV5804N, SVD5804N

TYPICAL PERFORMANCE CHARACTERISTICS

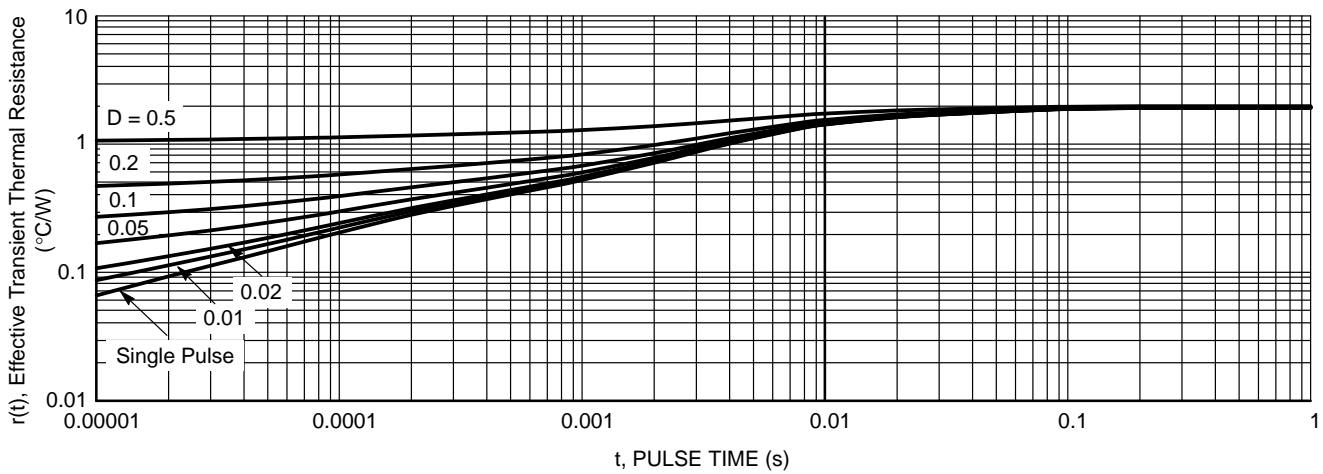


Figure 12. Thermal Response

ORDERING INFORMATION

Order Number	Package	Shipping [†]
NTD5804NT4G	DPAK (Pb-Free)	2500 / Tape & Reel
NTDV5804NT4G*	DPAK (Pb-Free)	2500 / Tape & Reel
STDV5804NT4G*	DPAK (Pb-Free)	2500 / Tape & Reel
SVD5804NT4G*	DPAK (Pb-Free)	2500 / Tape & Reel
SSVD5804NT4G*	DPAK (Pb-Free)	2500 / Tape & Reel

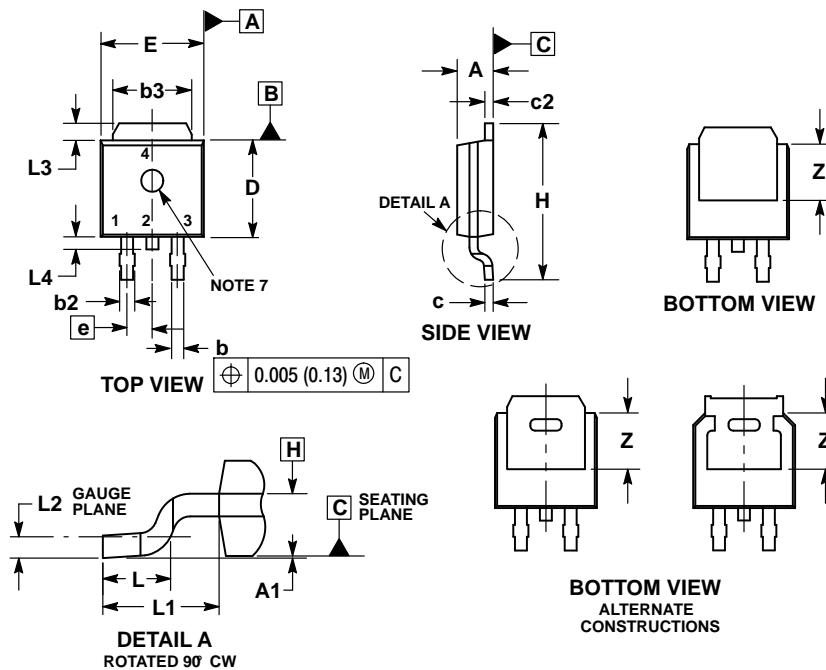
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NTDV, STDV and SVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

NTD5804N, NTDV5804N, SVD5804N

PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE) CASE 369C ISSUE F



NOTES:

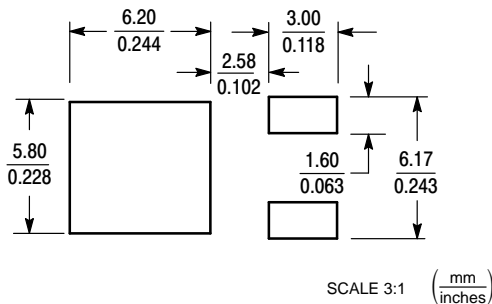
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE:

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

STYLE 2:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



SCALE 3:1 (mm/inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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